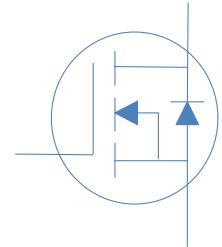


**80V N-Ch Power MOSFET**

$V_{DS}$	80	V
$R_{DS(on),typ}$	$V_{GS}=10V$	3.1 m
$R_{DS(on),typ}$	$V_{GS}=4.5V$	4.3 m
$I_D$ (Silicon Limited)	140	A
$I_D$ (Package Limited)	120	A



Part Number	Package	Marking
HGD035N08AL	TO-252	GD035N08AL



#### Absolute Maximum Ratings at $T_J=25^\circ C$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	$I_D$	$T_C=25^\circ C$	140	A
Continuous Drain Current (Package Limited)		$T_C=100^\circ C$	99	
		$T_C=25^\circ C$	120	
Drain to Source Voltage	$V_{DS}$	-	80	V
Gate to Source Voltage	$V_{GS}$	-	$\pm 20$	V
Pulsed Drain Current	$I_{DM}$	-	400	A
Avalanche Energy, Single Pulse	$E_{AS}$	$L=0.1mH, T_C=25^\circ C$	80	mJ
Power Dissipation	$P_D$	$T_C=25^\circ C$	150	W
Operating and Storage Temperature	$T_J, T_{stg}$	-	-55 to 175	°C

#### Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{JA}$	46	°C/W
Thermal Resistance Junction-Case	$R_{JC}$	1	°C/W



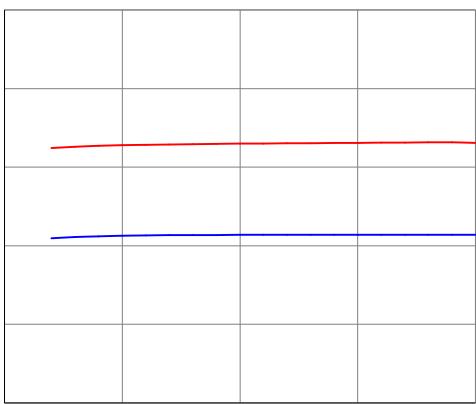
Fig 1. Typical Output Characteristics	Figure 2. On-Resistance vs. Gate-Source Voltage
Figure 3. On-Resistance vs. Drain Current and Gate Voltage	Figure 4. Normalized On-Resistance vs. Junction Temperature
	
Figure 5. Typical Transfer Characteristics	Figure 6. Typical Source-Drain Diode Forward Voltage

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

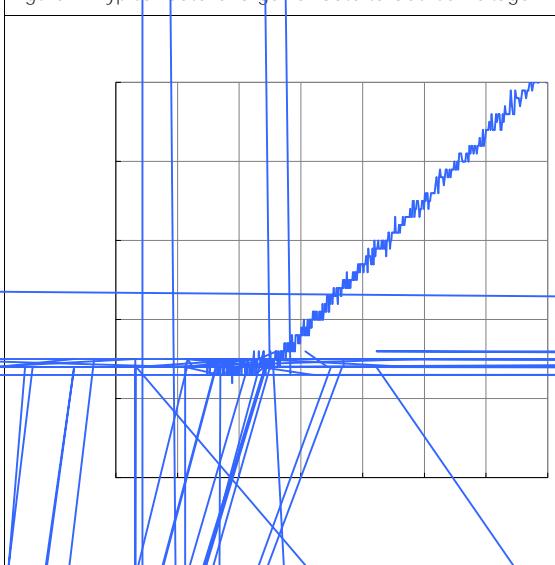


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

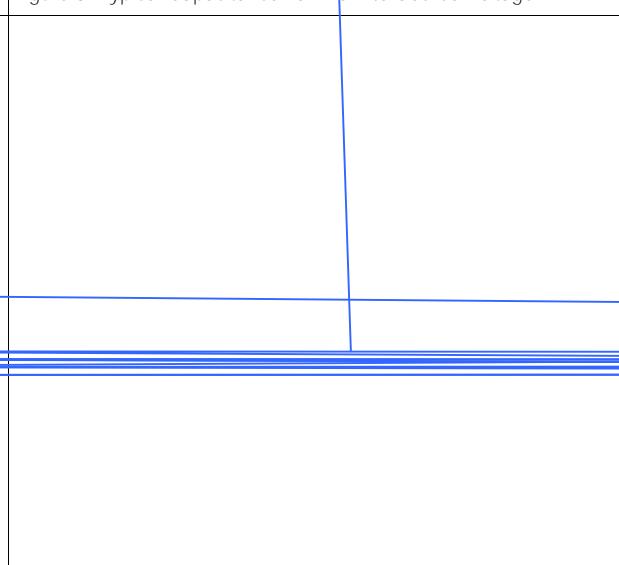


Figure 9. Maximum Safe Operating Area

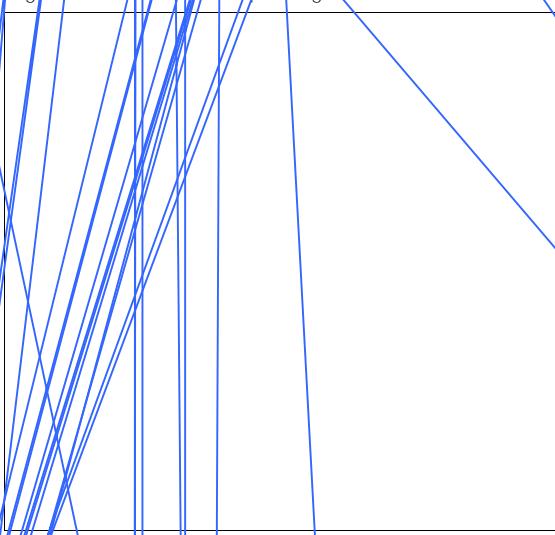


Figure 10. Maximum Drain Current vs. Case Temperature

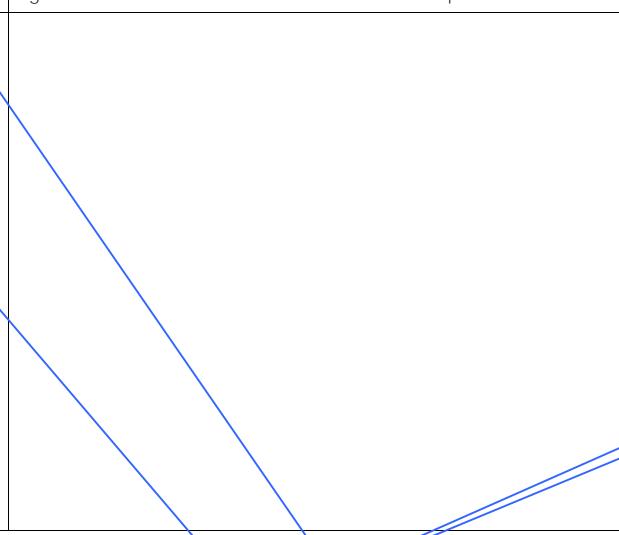
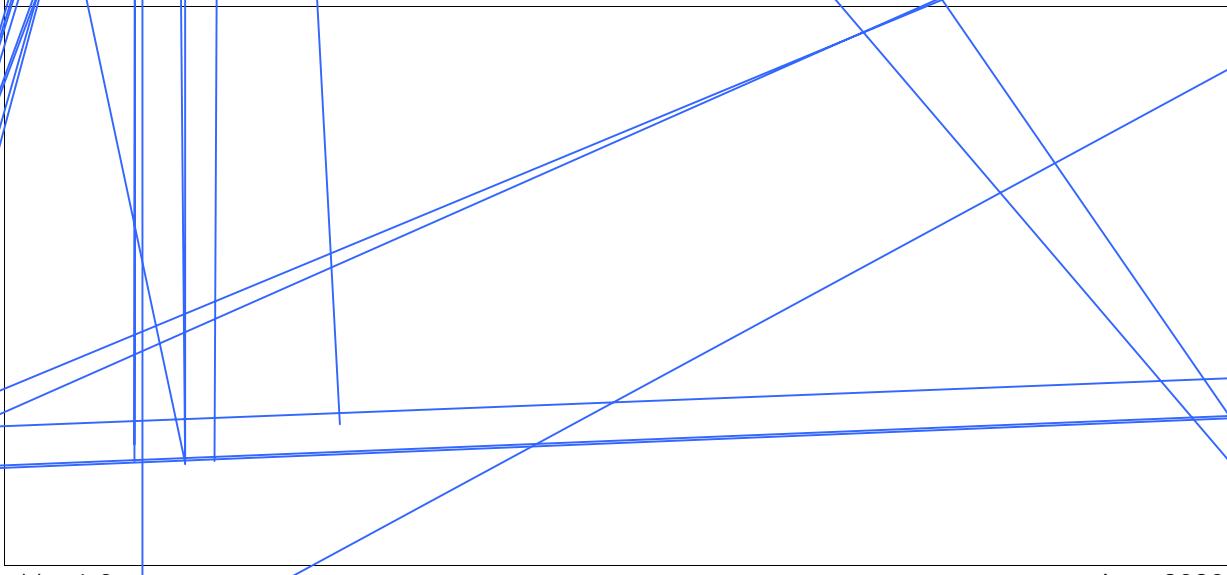
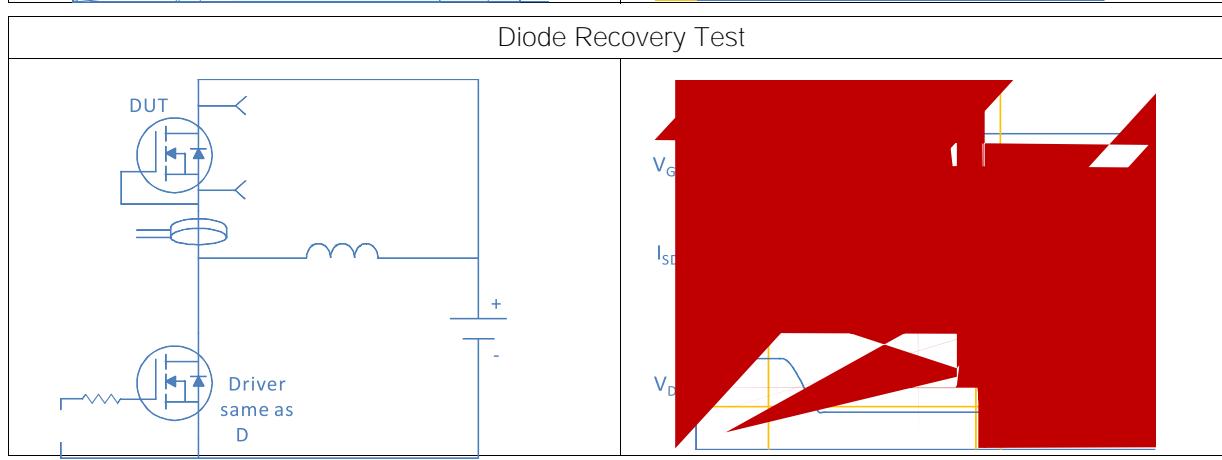
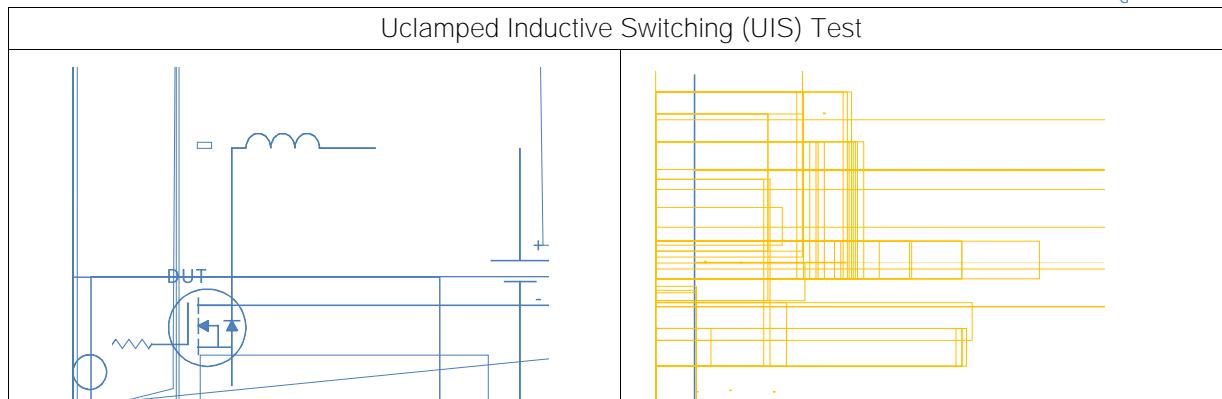
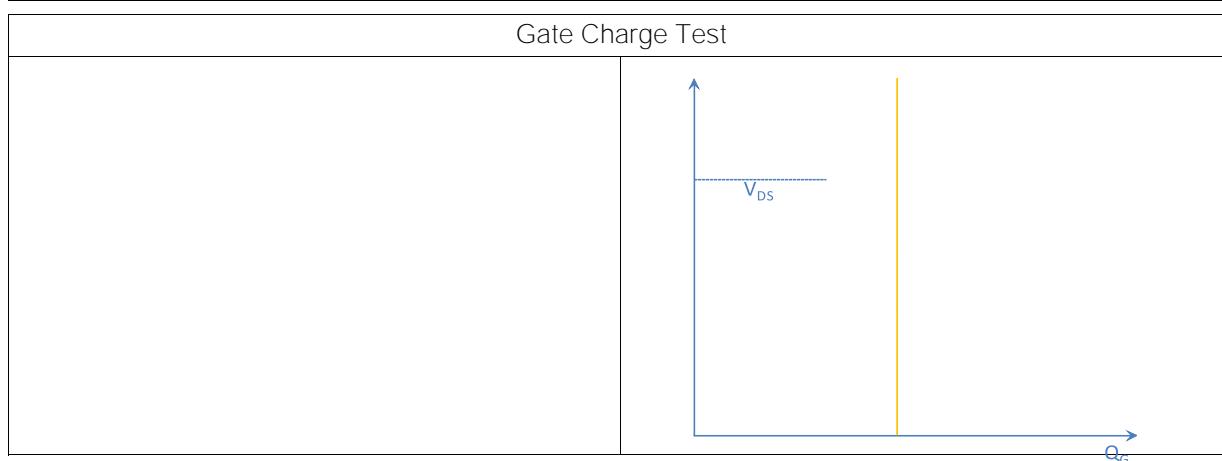
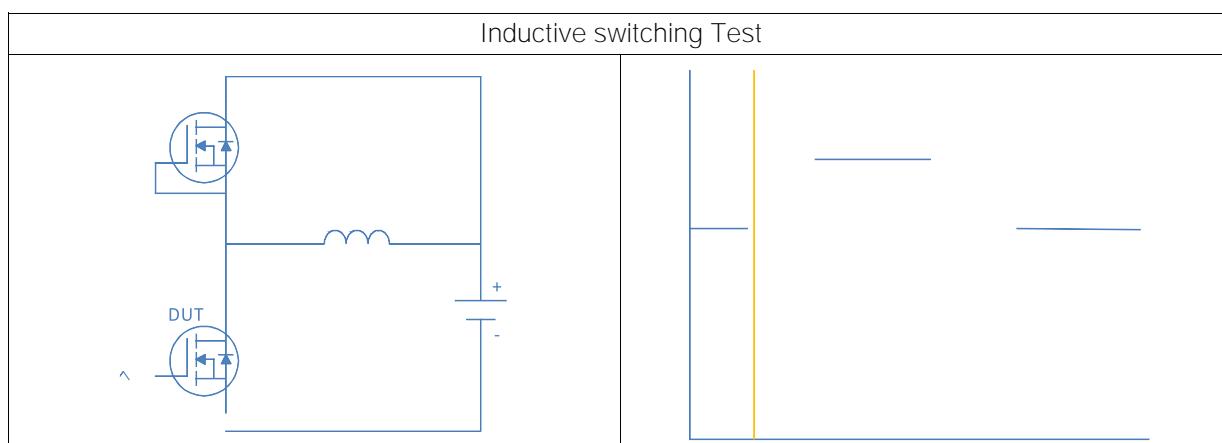


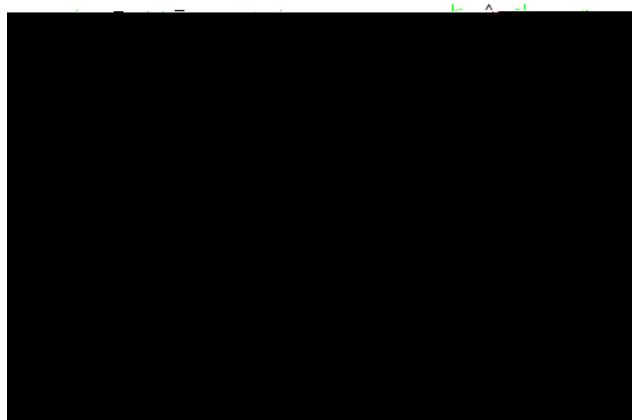
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient





## Package Outline

TO-252, 3 leads



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743	REF	
L2	0.508	BSC	
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223

